



60V N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8

Product Summary

| BV _{DSS} | R _{DS(ON)} Max | I _D Max T _C = +25°C |
|-------------------|-------------------------------|--|
| 201/ | 12mΩ @ V _{GS} = 10V | 43.3A |
| 60V | 15mΩ @ V _{GS} = 4.5V | 38.7A |

Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

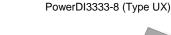
- Backlighting
- Power Management Functions
- DC-DC Converters

Features and Benefits

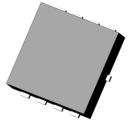
- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable and Robust End Application
- Low R_{DS(ON)} Ensures On-State Losses are Minimized
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Occupies just 33% of the Board Area Occupied by SO-8 Enabling Smaller End Product
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Mechanical Data

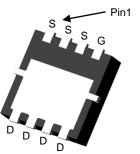
- Case: PowerDI[®]3333-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.030 grams (Approximate)



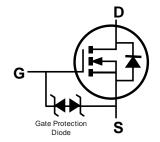








Bottom View



Internal Schematic

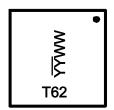
Ordering Information (Note 4)

| Part Number | Case | Packaging |
|---------------|-------------------------|---------------------|
| DMT6012LFV-7 | PowerDI3333-8 (Type UX) | 2,000/Tape and Reel |
| DMT6012LFV-13 | PowerDI3333-8 (Type UX) | 3,000/Tape and Reel |

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- See http://www.diodes.com/quality/lead_free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



T62= Product Type Marking Code

YYWW = Date Code Marking

YY = Last Two Digits of Year (ex: 18 = 2018)

WW = Week Code (01 to 53)



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

| Characteristic | Symbol | Value | Unit | |
|--|-----------------|----------------|--------------|---|
| Drain-Source Voltage | V_{DSS} | 60 | V | |
| Gate-Source Voltage | V_{GSS} | ±20 | V | |
| Continuous Drain Current (Note 6) $V_{GS} = 10V$ $T_{C} = +25^{\circ}C$ $T_{C} = +70^{\circ}C$ | | Ι _D | 43.3 34.7 | А |
| Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%) | I _{DM} | 170 | Α | |
| Maximum Continuous Body Diode Forward Current (Note 6) | Is | 40 | Α | |
| Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%) | I _{SM} | 170 | Α | |
| Avalanche Current, L = 0.1mH | I _{AS} | 23.7 | Α | |
| Avalanche Energy, L = 0.1mH | E _{AS} | 28.1 | mJ | |

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

| Characteristic | | Symbol | Value | Unit |
|---|----------------|----------------------------------|-------------|------|
| Total Power Dissipation (Note 5) | $T_A = +25$ °C | P_{D} | 1.95 | W |
| Thermal Resistance, Junction to Ambient (Note 5) | | $R_{	heta JA}$ | 64 | |
| Total Power Dissipation (Note 6) $T_C = +25^{\circ}C$ | | P _D | 33.78 | °C/W |
| Thermal Resistance, Junction to Case (Note 6) | | $R_{\theta JC}$ | 3.7 | |
| Operating and Storage Temperature Range | | T _{J,} T _{STG} | -55 to +150 | °C |

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

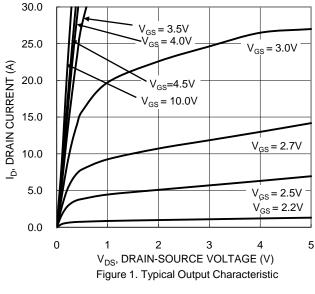
| Characteristic | Symbol | Min | Тур | Max | Unit | Test Condition | |
|--|---------------------|-----|------|-----|-------|---|--|
| OFF CHARACTERISTICS (Note 7) | | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | 60 | _ | _ | V | $V_{GS} = 0V$, $I_D = 1mA$ | |
| Zero Gate Voltage Drain Current | I _{DSS} | | _ | 1 | μA | $V_{DS} = 48V, V_{GS} = 0V$ | |
| Gate-Source Leakage | I _{GSS} | _ | _ | ±10 | μΑ | $V_{GS} = \pm 20V, V_{DS} = 0V$ | |
| ON CHARACTERISTICS (Note 7) | | | | | | | |
| Gate Threshold Voltage | V _{GS(TH)} | 1 | _ | 2.5 | V | $V_{DS} = V_{GS}, I_{D} = 250 \mu A$ | |
| Static Drain-Source On-Resistance | | _ | 8.2 | 12 | mΩ | $V_{GS} = 10V, I_D = 20A$ | |
| Static Diani-Source On-Resistance | R _{DS(ON)} | | 11.2 | 15 | 11122 | $V_{GS} = 4.5V, I_D = 12.5A$ | |
| Diode Forward Voltage | V_{SD} | _ | 0.8 | 1.2 | V | $V_{GS} = 0V, I_{S} = 20A$ | |
| DYNAMIC CHARACTERISTICS (Note 8) | | | | | | | |
| Input Capacitance | C _{iss} | _ | 1522 | _ | | $V_{DS} = 30V$, $V_{GS} = 0V$, $f = 1MHz$ | |
| Output Capacitance | Coss | 1 | 352 | _ | pF | | |
| Reverse Transfer Capacitance | C _{rss} | | 27.5 | _ | | | |
| Gate Resistance | R_g | - | 1.4 | _ | Ω | $V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$ | |
| Total Gate Charge (V _{GS} = 4.5V) | Q_g | _ | 10.7 | _ | | | |
| Total Gate Charge (V _{GS} = 10V) | Q_g | _ | 22.2 | _ | nC | $V_{DS} = 30V, I_{D} = 10A$ | |
| Gate-Source Charge | Q_{gs} | | 3.3 | _ | IIC | | |
| Gate-Drain Charge | Q_{gd} | _ | 4.2 | _ | | | |
| Turn-On Delay Time | t _{D(ON)} | _ | 4.4 | _ | | $V_{GS} = 10V, V_{DS} = 30V,$ $R_g = 6\Omega, I_D = 10A$ | |
| Turn-On Rise Time | t _R | _ | 6.7 | _ | | | |
| Turn-Off Delay Time | t _{D(OFF)} | - | 25.5 | _ | ns | | |
| Turn-Off Fall Time | t _F | _ | 12.5 | _ | | | |
| Reverse Recovery Time | t _{RR} | _ | 25.8 | _ | ns | 1 400 4:/44 4000/ | |
| Reverse Recovery Charge | Q _{RR} | _ | 15.1 | _ | nC | $I_F = 10A$, di/dt = 100A/ μ s | |

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.

^{6.} Thermal resistance from junction to soldering point (on the exposed drain pad).7. Short duration pulse test used to minimize self-heating effect.

^{8.} Guaranteed by design. Not subject to product testing.





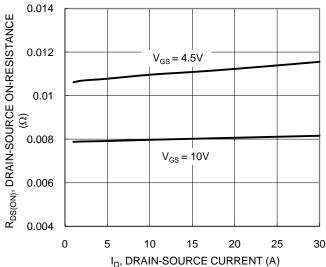
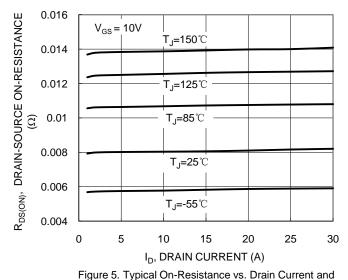


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage



Junction Temperature

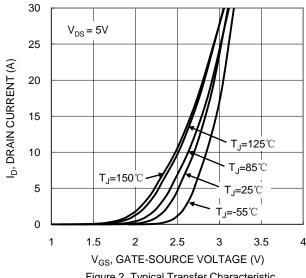


Figure 2. Typical Transfer Characteristic

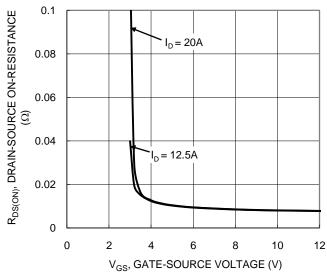


Figure 4. Typical Transfer Characteristic

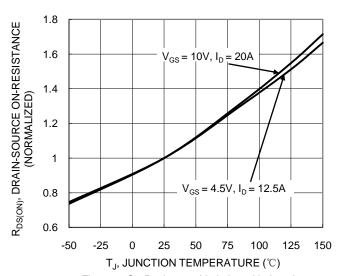


Figure 6. On-Resistance Variation with Junction Temperature



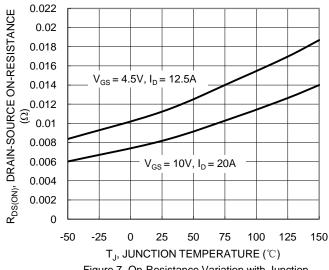


Figure 7. On-Resistance Variation with Junction Temperature

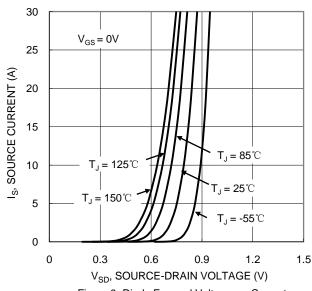


Figure 9. Diode Forward Voltage vs. Current

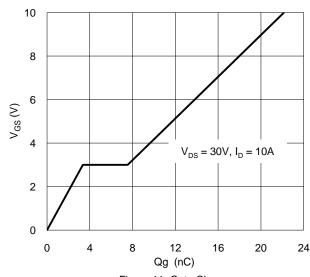


Figure 11. Gate Charge

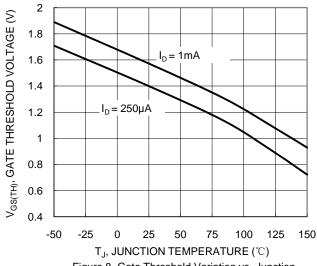
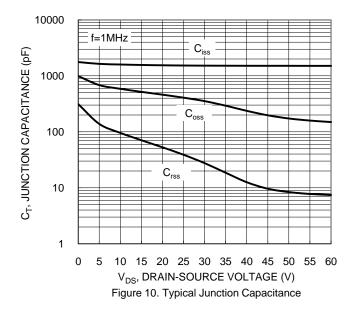


Figure 8. Gate Threshold Variation vs. Junction Temperature



1000 $R_{DS(ON)}$ Limited 100 I_D, DRAIN CURRENT (A) 10 P_W =10μs P_W =100μs T_{J(Max)} = 150°C T_C = 25°C Single Pulse $P_W = 100 ms$ 0.1 DUT on Infinite DC Heatsink $V_{GS} = 10V$ 0.01 0.1 10 100 V_{DS}, DRAIN-SOURCE VOLTAGE (V) Figure 12. SOA, Safe Operation Area



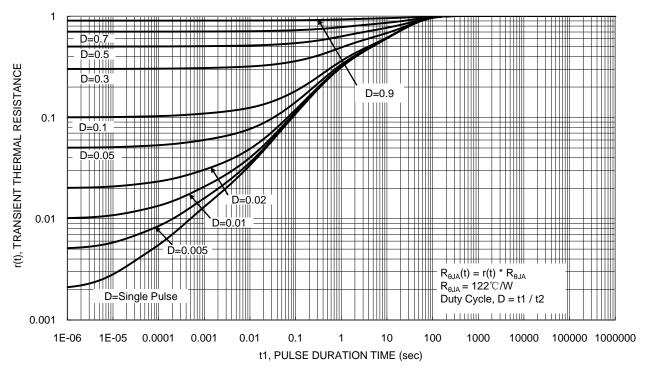


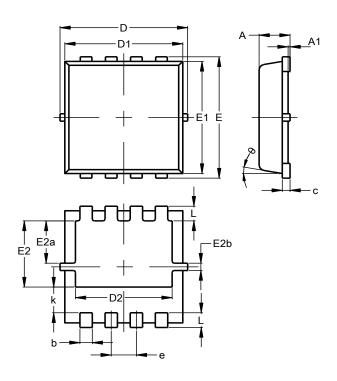
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (Type UX)

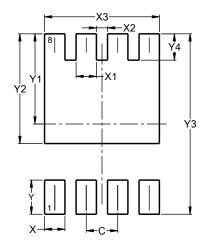


| PowerDl3333-8 (Type UX) | | | | | |
|----------------------------|----------|------|------|--|--|
| Dim | Min | Max | Тур | | |
| Α | 0.75 | 0.85 | 0.80 | | |
| A1 | 0.00 | 0.05 | | | |
| b | 0.25 | 0.40 | 0.32 | | |
| С | 0.10 | 0.25 | 0.15 | | |
| D | 3.20 | 3.40 | 3.30 | | |
| D1 | 2.95 | 3.15 | 3.05 | | |
| D2 | 2.30 | 2.70 | 2.50 | | |
| E | 3.20 | 3.40 | 3.30 | | |
| E1 | 2.95 | 3.15 | 3.05 | | |
| E2 | 1.60 | 2.00 | 1.80 | | |
| E2a | 0.95 | 1.35 | 1.15 | | |
| E2b | 0.10 | 0.30 | 0.20 | | |
| е | 0.65 BSC | | | | |
| k | 0.50 | 0.90 | 0.70 | | |
| L | 0.30 | 0.50 | 0.40 | | |
| θ | 0° | 12° | 10° | | |
| All Dimensions in mm | | | | | |

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (Type UX)



| Dimensions | Value (in mm) | | |
|------------|---------------|--|--|
| С | 0.650 | | |
| X | 0.420 | | |
| X1 | 0.420 | | |
| X2 | 0.230 | | |
| Х3 | 2.370 | | |
| Y | 0.700 | | |
| Y1 | 1.850 | | |
| Y2 | 2.250 | | |
| Y3 | 3.700 | | |
| Y4 | 0.540 | | |



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